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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

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Art Unit: 2829

Shunpei YAMAZAKI et al.

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Examiner: A Sakar

Serial No. 09/699,466 ✓

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Filed: October 31, 2000 ✓

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For: METHOD FOR FABRICATING A

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SEMICONDUCTOR DEVICE

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CERTIFICATE OF MAILING

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AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated August 6, 2002 please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claims 4-34 and amend claim 1 as follows:

1. (Amended) A method for manufacturing a semiconductor device comprising:
- forming a semiconductor film on an insulating surface;
  - forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface;
  - forming a first gate insulating film over the semiconductor island wherein the first gate insulating film comprises silicon oxide;
  - forming a second gate insulating film over the first gate insulating film wherein the second gate insulating film comprises silicon oxide nitride;
  - forming a gate electrode over the semiconductor island with the first gate insulating film and the second gate insulating film therebetween; and

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